



NTH027N65S3F

N-Channel SuperFET® III FRFET® MOSFET 650 V, 75 A, 27.4 mΩ

Features

- 700 V @ $T_J = 150^\circ\text{C}$
- Typ. $R_{DS(on)} = 23\text{ m}\Omega$
- Ultra Low Gate Charge (Typ. $Q_g = 259\text{ nC}$)
- Low Effective Output Capacitance (Typ. $C_{oss(eff.)} = 1972\text{ pF}$)
- 100% Avalanche Tested
- RoHS Compliant

Applications

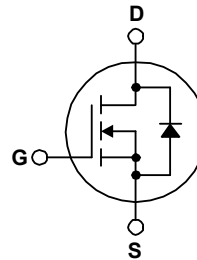
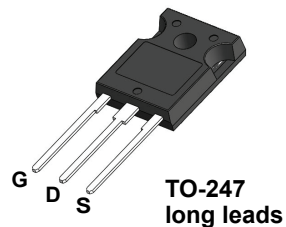
- Telecom / Server Power Supplies
- Industrial Power Supplies
- UPS / Solar

Description

SuperFET® III MOSFET is ON Semiconductor's brand-new high voltage super-junction (SJ) MOSFET family that is utilizing charge balance technology for outstanding low on-resistance and lower gate charge performance. This advanced technology is tailored to minimize conduction loss, provide superior switching performance, and withstand extreme dv/dt rate.

Consequently, SuperFET III MOSFET is very suitable for the various power system for miniaturization and higher efficiency.

SuperFET III FRFET® MOSFET's optimized reverse recovery performance of body diode can remove additional component and improve system reliability.



Absolute Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	NTH027N65S3F_F155 (Note 1)	Unit
V_{DSS}	Drain to Source Voltage	650	V
V_{GSS}	Gate to Source Voltage	- DC	± 30
		- AC ($f > 1\text{ Hz}$)	± 30
I_D	Drain Current	- Continuous ($T_C = 25^\circ\text{C}$)	75
		- Continuous ($T_C = 100^\circ\text{C}$)	60
I_{DM}	Drain Current	- Pulsed (Note 2)	187.5
E_{AS}	Single Pulsed Avalanche Energy	(Note 3)	1610
I_{AS}	Avalanche Current	(Note 2)	15
E_{AR}	Repetitive Avalanche Energy	(Note 2)	5.95
dv/dt	MOSFET dv/dt		100
	Peak Diode Recovery dv/dt (Note 4)		50
P_D	Power Dissipation	($T_C = 25^\circ\text{C}$)	595
		- Derate Above 25°C	4.76
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to +150	$^\circ\text{C}$
T_L	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds	300	$^\circ\text{C}$

Thermal Characteristics

Symbol	Parameter	NTH027N65S3F_F155	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	0.21	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient, Max.	40	

Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
NTH027N65S3F_F155	NTH027N65S3F	TO-247	Tube	N/A	N/A	30 units

Electrical Characteristics $T_C = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
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Off Characteristics

BV _{DSS}	Drain to Source Breakdown Voltage	V _{GS} = 0 V, I _D = 1 mA, T _J = 25°C	650	-	-	V
		V _{GS} = 0 V, I _D = 1 mA, T _J = 150°C	700	-	-	V
$\Delta BV_{DSS} / \Delta T_J$	Breakdown Voltage Temperature Coefficient	I _D = 15 mA, Referenced to 25°C	-	0.61	-	V/°C
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 650 V, V _{GS} = 0 V	-	-	10	μA
		V _{DS} = 520 V, T _C = 125°C	-	361	-	
I _{GSS}	Gate to Body Leakage Current	V _{GS} = ±30 V, V _{DS} = 0 V	-	-	±100	nA

On Characteristics

V _{GS(th)}	Gate Threshold Voltage	V _{GS} = V _{DS} , I _D = 7.5 mA	3.0	-	5.0	V
R _{DS(on)}	Static Drain to Source On Resistance	V _{GS} = 10 V, I _D = 35 A	-	23	27.4	mΩ
g _{FS}	Forward Transconductance	V _{DS} = 20 V, I _D = 37.5 A	-	56	-	S

Dynamic Characteristics

C _{iss}	Input Capacitance	V _{DS} = 400 V, V _{GS} = 0 V, f = 1 MHz	-	7690	-	pF	
C _{oss}	Output Capacitance		-	200	-	pF	
C _{oss(eff.)}	Effective Output Capacitance	V _{DS} = 0 V to 400 V, V _{GS} = 0 V	-	1972	-	pF	
C _{oss(er.)}	Energy Related Output Capacitance	V _{DS} = 0 V to 400 V, V _{GS} = 0 V	-	352	-	pF	
Q _{g(tot)}	Total Gate Charge at 10V	V _{DS} = 400 V, I _D = 37.5 A, V _{GS} = 10 V	-	259	-	nC	
Q _{gs}	Gate to Source Gate Charge		-	72	-	nC	
Q _{gd}	Gate to Drain "Miller" Charge		(Note 5)	-	99	-	nC
ESR	Equivalent Series Resistance		f = 1 MHz	-	1.2	-	Ω

Switching Characteristics

t _{d(on)}	Turn-On Delay Time	V _{DD} = 400 V, I _D = 37.5 A, V _{GS} = 10 V, R _g = 2 Ω	-	49	-	ns
t _r	Turn-On Rise Time		-	47	-	ns
t _{d(off)}	Turn-Off Delay Time		-	131	-	ns
t _f	Turn-Off Fall Time		(Note 5)	-	34	-

Source-Drain Diode Characteristics

I _S	Maximum Continuous Source to Drain Diode Forward Current	-	-	75	A	
I _{SM}	Maximum Pulsed Source to Drain Diode Forward Current	-	-	187.5	A	
V _{SD}	Source to Drain Diode Forward Voltage	V _{GS} = 0 V, I _{SD} = 37.5 A	-	-	1.3	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0 V, I _{SD} = 37.5 A,	-	168	-	ns
Q _{rr}	Reverse Recovery Charge	dI _F /dt = 100 A/μs	-	1014	-	nC

Notes:

1. Due to system integration constraints between Fairchild and ON semiconductor, as of November 1, 2017 any product part number with a underscore will be replaced with a dash. This is a notification.
2. Repetitive rating: pulse-width limited by maximum junction temperature.
3. I_{AS} = 15 A, R_G = 25 Ω, starting T_J = 25°C.
4. I_{SD} ≤ 37.5 A, di/dt ≤ 100 A/μs, V_{DD} ≤ 400 V, starting T_J = 25°C.
5. Essentially independent of operating temperature typical characteristics.

Typical Performance Characteristics

Figure 1. On-Region Characteristics

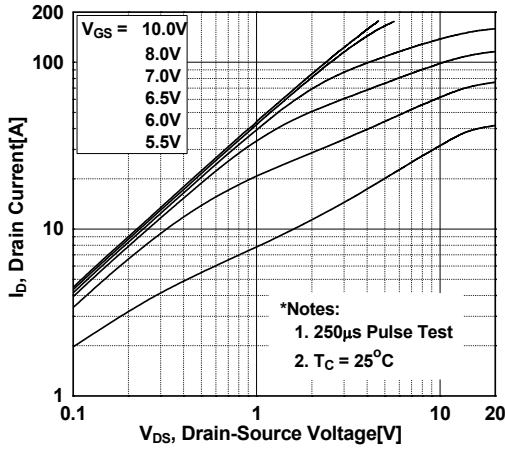


Figure 2. Transfer Characteristics

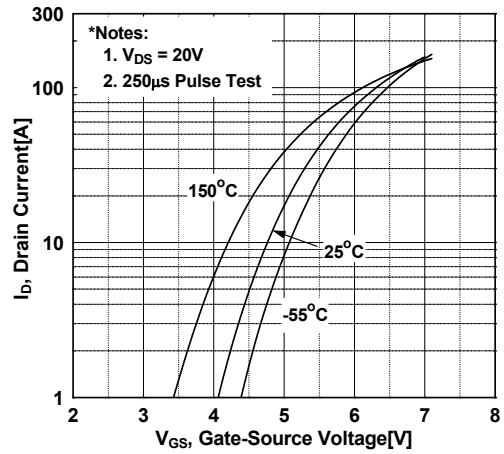


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

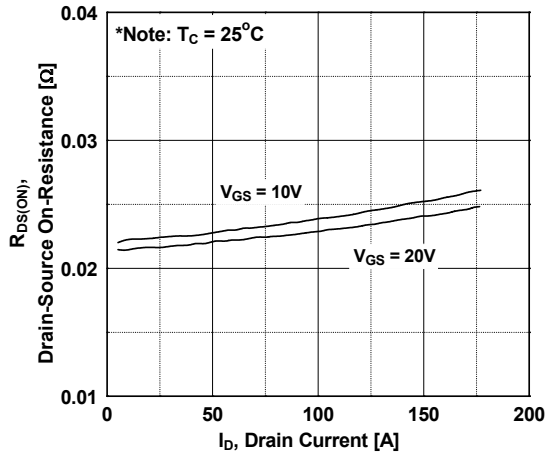


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

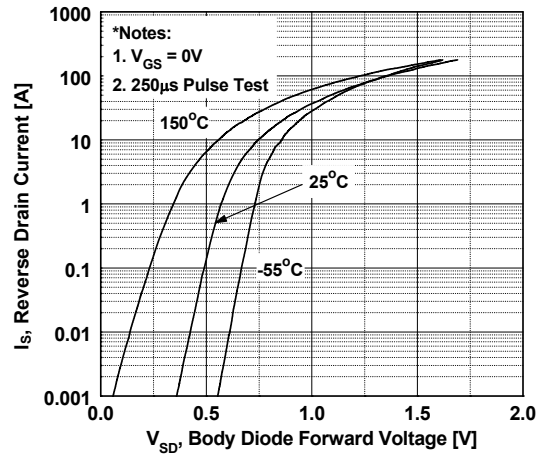


Figure 5. Capacitance Characteristics

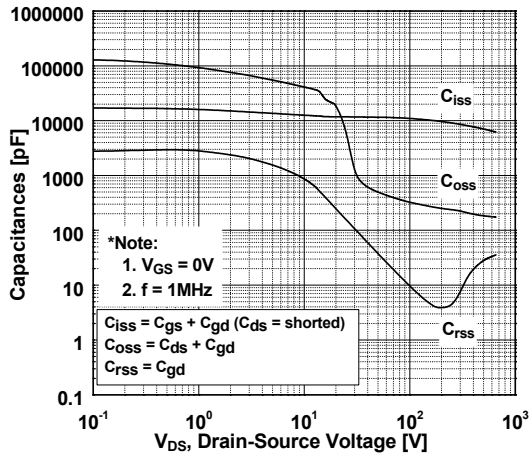
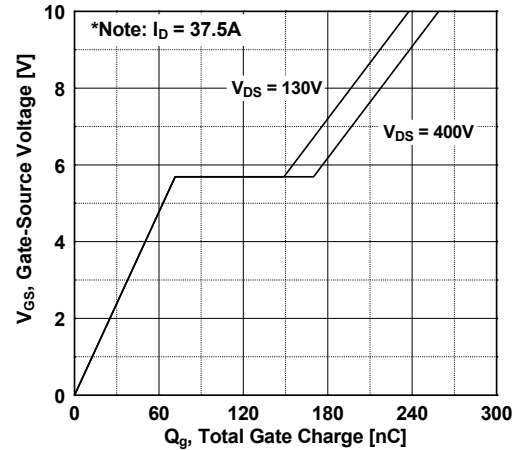


Figure 6. Gate Charge Characteristics



Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

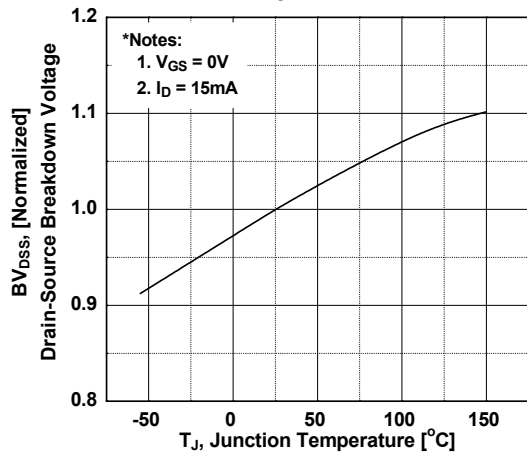


Figure 8. On-Resistance Variation vs. Temperature

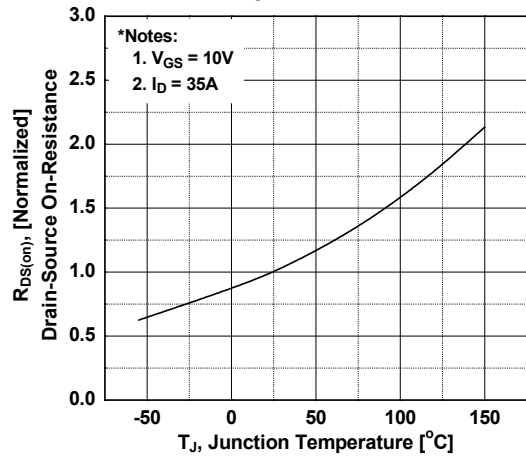


Figure 9. Maximum Safe Operating Area

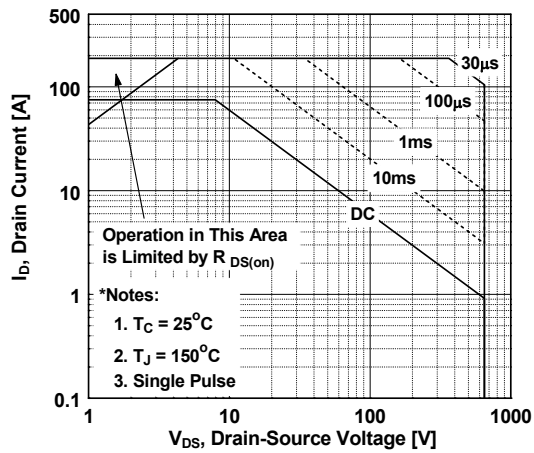


Figure 10. Maximum Drain Current vs. Case Temperature

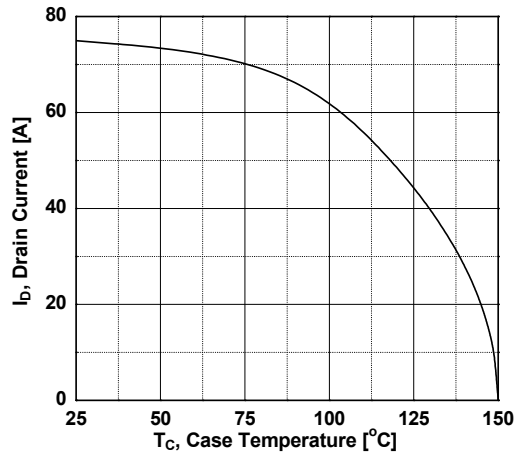
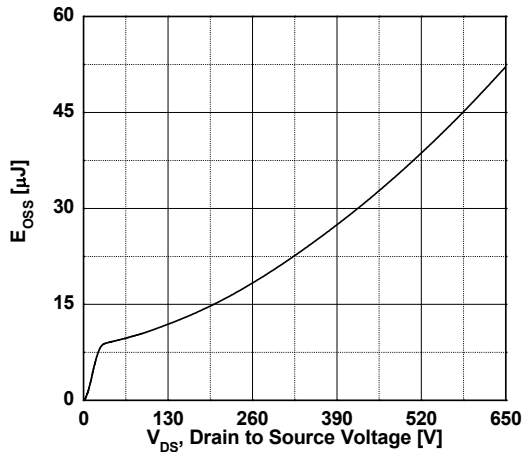
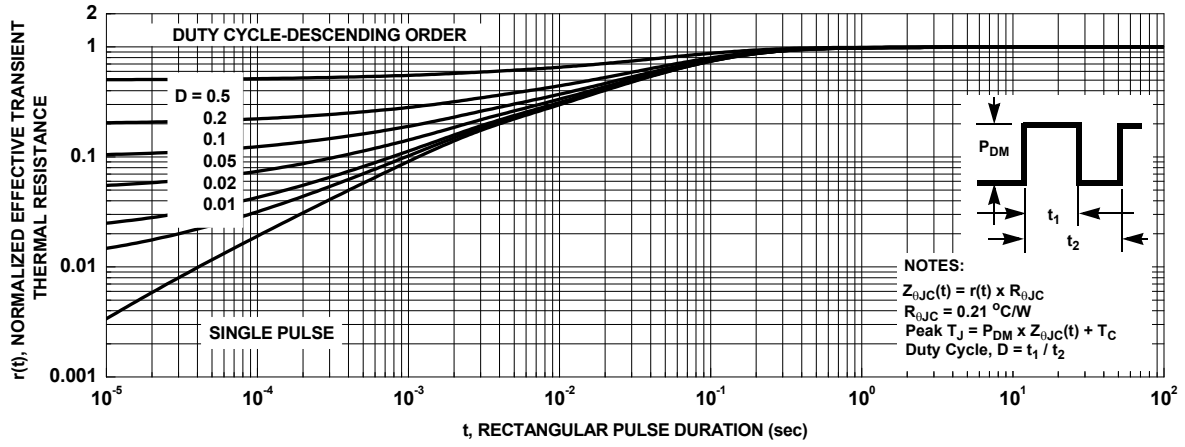


Figure 11. Eoss vs. Drain to Source Voltage



Typical Performance Characteristics (Continued)

Figure 12. Transient Thermal Response Curve



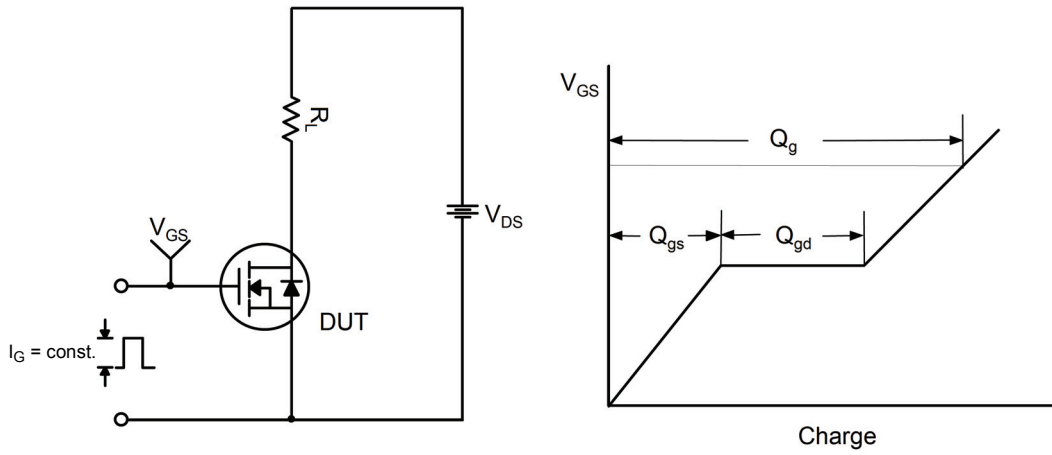


Figure 13. Gate Charge Test Circuit & Waveform

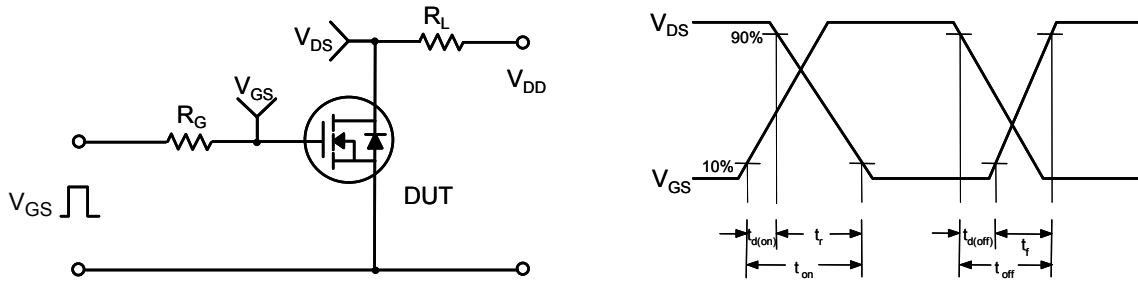


Figure 14. Resistive Switching Test Circuit & Waveforms



Figure 15. Unclamped Inductive Switching Test Circuit & Waveforms

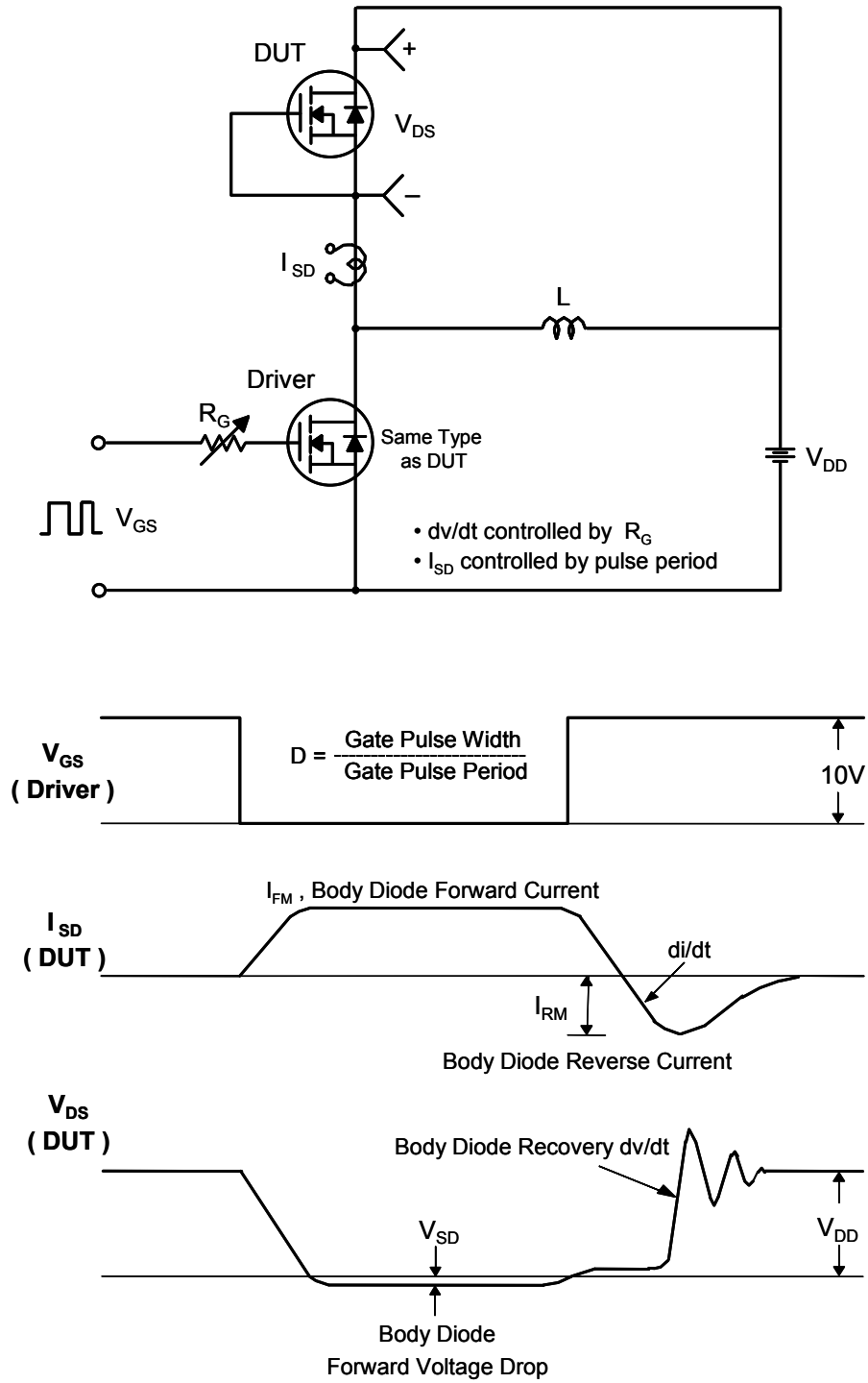
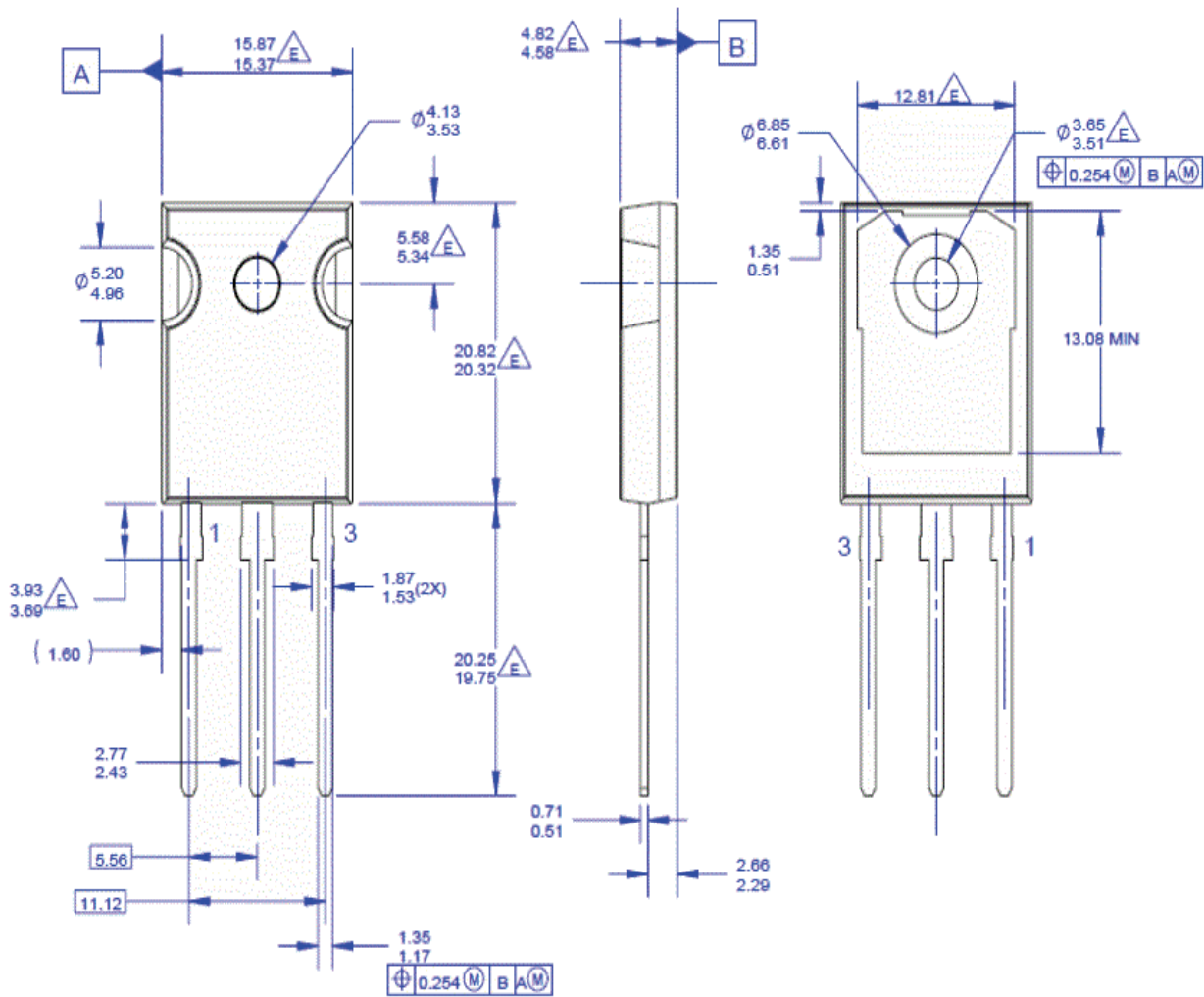


Figure 16. Peak Diode Recovery dv/dt Test Circuit & Waveforms

Mechanical Dimensions



NOTES: UNLESS OTHERWISE SPECIFIED.

- A. PACKAGE REFERENCE: JEDEC TO-247, ISSUE E, VARIATION AB, DATED JUNE, 2004.
- B. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSIONS.
- C. ALL DIMENSIONS ARE IN MILLIMETERS.
- D. DRAWING CONFORMS TO ASME Y14.5 - 1994

E DOES NOT COMPLY JEDEC STANDARD VALUE
 F. DRAWING FILENAME: MKT-TO247G03_REV02

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